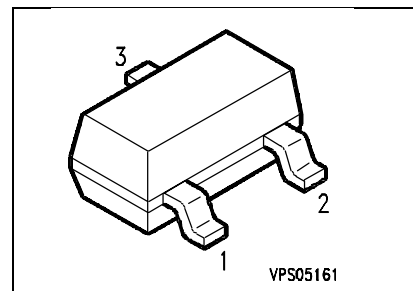


Silicon PIN Diode

- High voltage current controlled
- RF resistor for RF attenuator and switches
- Frequency range above 1 MHz
- Low resistance and short carrier lifetime
- For frequencies up to 3 GHz



Type	Marking	Ordering code (tape and reel)	Pin configuration			Package ¹⁾
			1	2	3	
BAR 64	POs	Q62702-A1041	A	-	C	SOT-23
BAR 64-04	PPs	Q62702-A1010	A	C	C/A	
BAR 64-05	PRs	Q62702-A1042	A	A	C/C	
BAR 64-06	PSs	Q62702-A1043	C	C	A/A	

Maximum ratings per diode

Parameter	Symbol	BAR 64	Unit
Reverse voltage	V_R	200	V
Forward current	I_F	100	mA
Total Power dissipation $T_S \leq 90^\circ\text{C}$	P_{tot}	250	mW
BAR64-04,-05,-06 $T_S \leq 65^\circ\text{C}$		250	
Junction temperature	T_j	150	$^\circ\text{C}$
Operating temperature range	T_{op}	-55 +150 $^\circ\text{C}$	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55...+150 $^\circ\text{C}$	$^\circ\text{C}$

Thermal resistance

Junction-ambient ¹⁾	$R_{\text{th JA}}$		K/W
BAR64		≤ 320	
BAR64-04,-05,-06		≤ 500	
Junction-soldering point	$R_{\text{th JS}}$		
BAR64		≤ 240	
BAR64-04,-05,-06		≤ 340	

¹⁾Package mounted on alumina 15mm x 16.7mm x 0.7mm

Electrical characteristics

at $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified.

Parameter	Symbol	Value			Unit
		min.	typ.	max.	

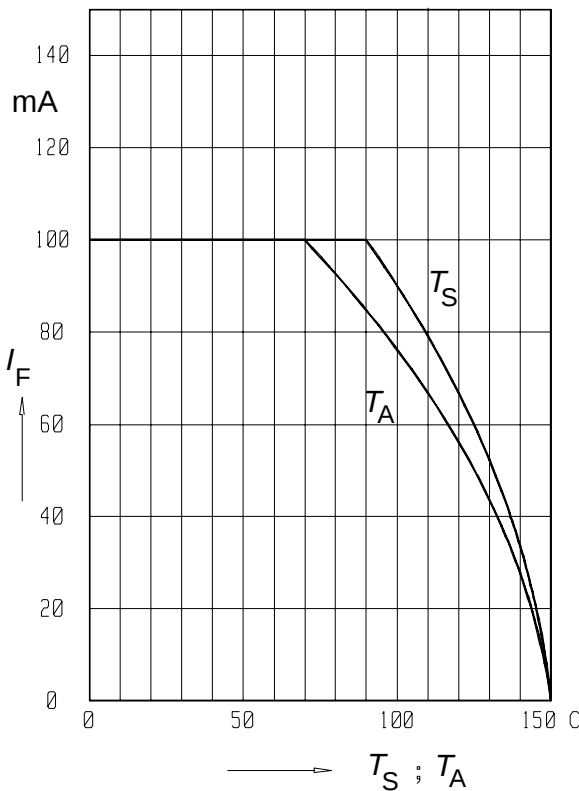
DC characteristics per diode

Breakdown voltage $I_R = 5\text{ }\mu\text{A}$	$V_{(BR)}$	200	-	-	V
Forward voltage $I_F = 50\text{ mA}$	V_F	-	-	1.1	V
Diode capacitance $V_R = 20\text{ V}$, $f = 1\text{ MHz}$	C_T	-	0.23	0.35	pF
Forward resistance $I_F = 1\text{ mA}$, $f = 100\text{ MHz}$ $I_F = 10\text{ mA}$, $f = 100\text{ MHz}$ $I_F = 100\text{ mA}$, $f = 100\text{ MHz}$	r_f	- --	12.5 2.1 0.85	20 3.8 1.35	Ω
Charge carrier lifetime $I_F = 10\text{ mA}$, $I_R = 6\text{ mA}$, $I_R = 3\text{ mA}$	τ_L	-	1.55	-	μs
Series inductance	L_S	-	1.4	-	nH

Forward current $r_F = f(T_S; T_A^*)$

* mounted on alumina

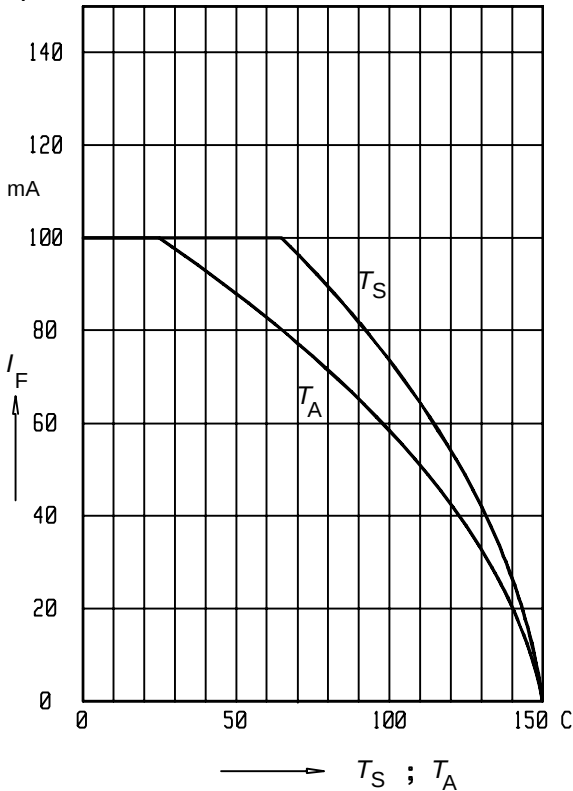
BAR64



Forward current $r_F = f(T_S; T_A^*)$

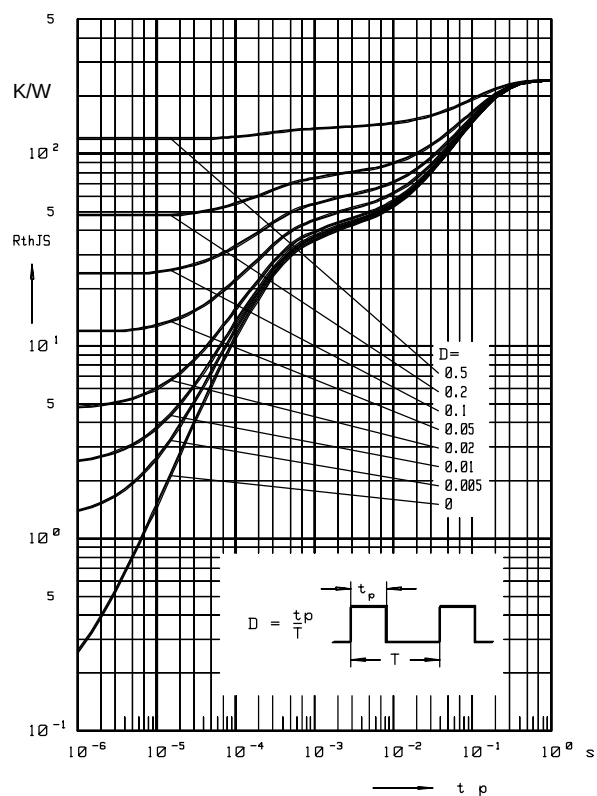
per each diode

BAR64-05,-05,-06



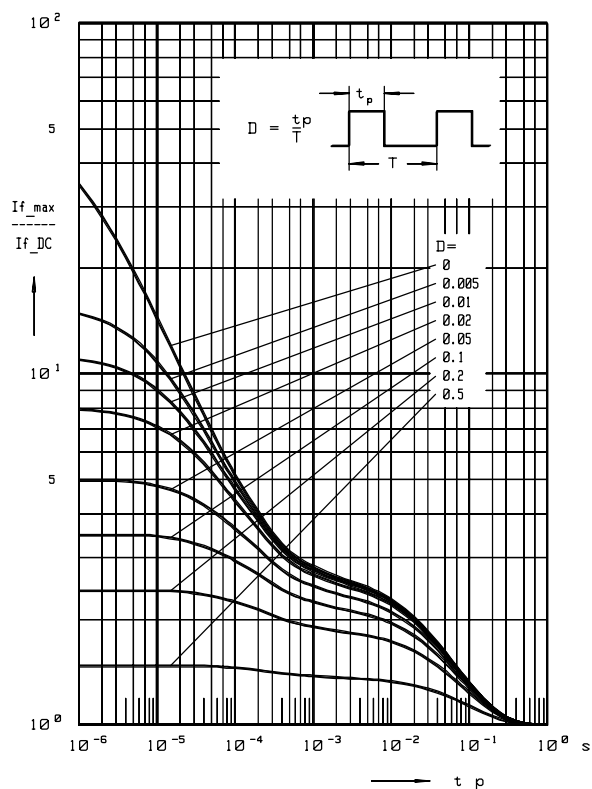
Permissible pulse load $R_{thJS} = f(t_p)$

BAR64



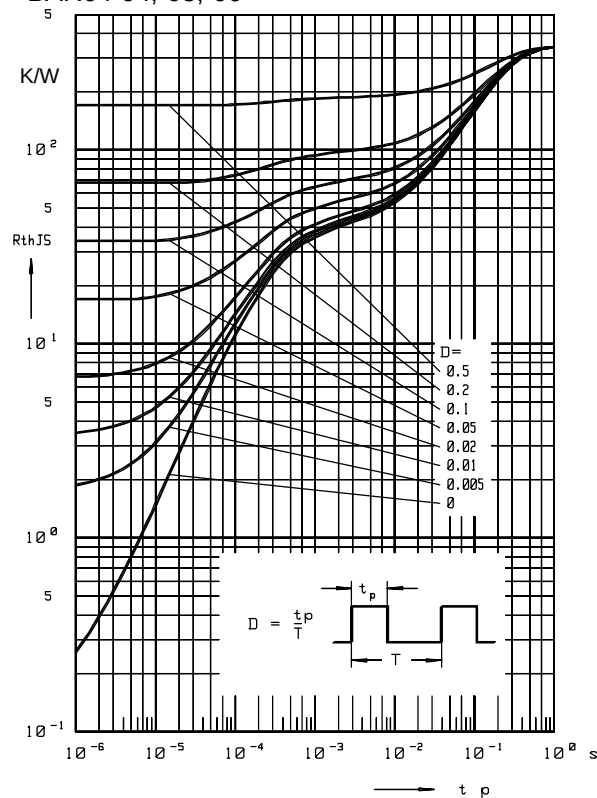
Permissible pulse load $I_{fmax}/I_{fDC} = f(t_p)$

BAR64



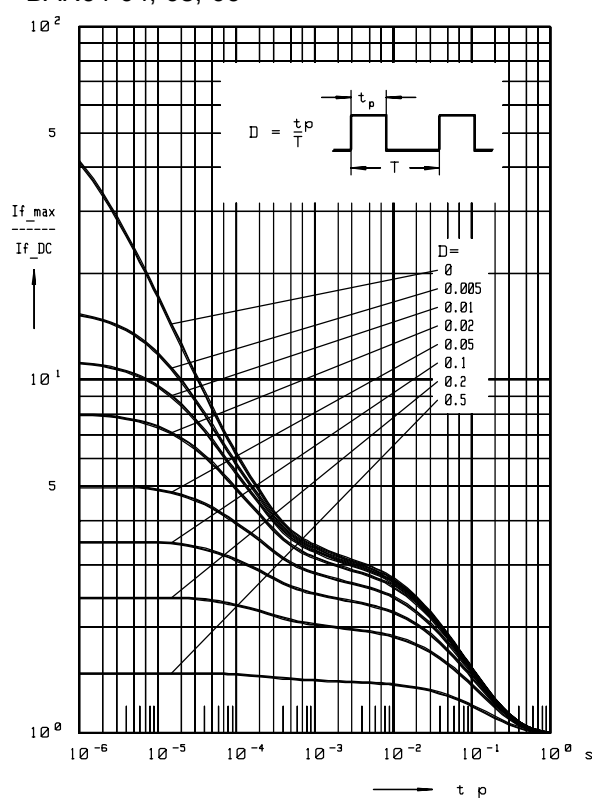
Permissible pulse load $R_{thJS} = f(t_p)$

BAR64-04,-05,-06

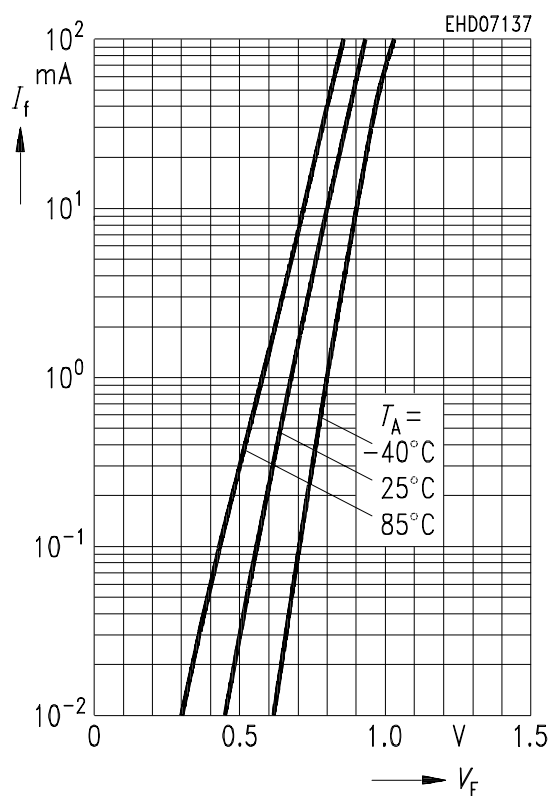


Permissible pulse load $I_{Fmax}/I_{FDC} = f(t_p)$

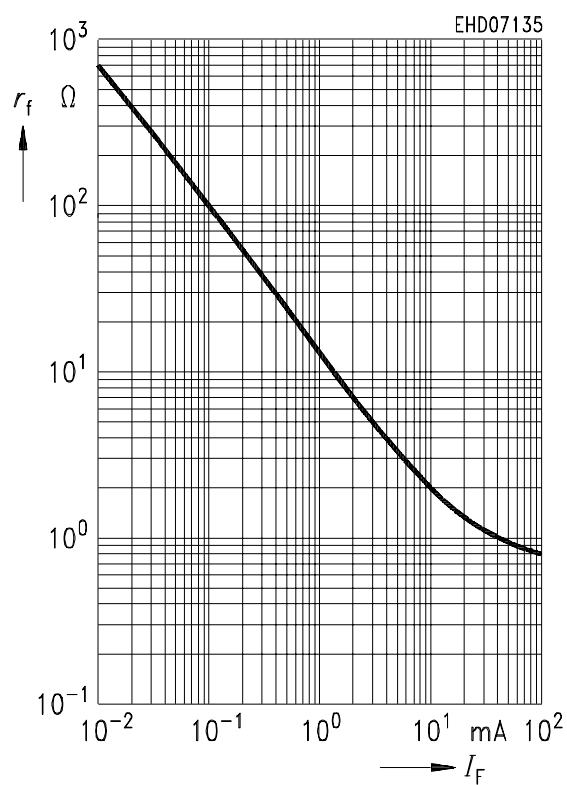
BAR64-04,-05,-06



Forward current $I_F = f(V_F)$



Forward resistance $r_f = f(I_F)$
 $f = 100 \text{ MHz}$



Diode capacitance $C_T = f(V_R)$
 $f = 1 \text{ MHz}$

